

CA3273

High-Side Driver

April 1994

Features

- Equivalent High Pass P-N-P Transistor
- Current Limiting.....0.6A to 1.2A
- Over-Voltage Shutdown+25V to +40V
- Junction Temperature Thermal Limit.....+150°C
- Equivalent Beta of 25...... 400mA/0.5V
- Internal Bandgap Voltage and Current Reference

Applications

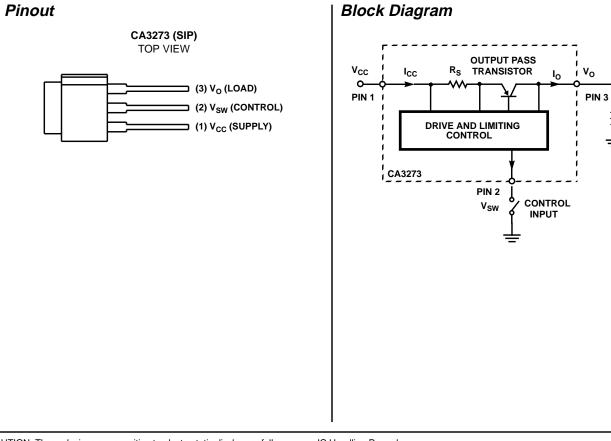
- Fuel Pump Driver
- Relay Driver
- Solenoid Driver
- Stepper Motor Driver
- Remote Power Switch
- Logic Control Switch

Description

The CA3273 is a power IC equivalent of a P-N-P pass transistor operated as a high-side-driver current switch in either the saturated (ON) or cutoff (OFF) modes. The CA3273 incorporates circuitry to protect the pass currents, excessive input voltage, and thermal overstress. The high-side driver is intended for general purpose, automotive and potentially high-stress applications. If high-stress conditions exist, the use of an external zener diode of 35V or less between supply and load terminals may be required to prevent damage due to severe conditions (such as load dump, reverse battery and positive or negative transients). The CA3273 is designed to withstand a nominal reverse-battery (VBAT = 13V) condition without permanent damage to the IC. The CA3273 is supplied in a modified 3-lead TO-202 plastic power package.

Ordering Information

PART NUMBER	TEMPERATURE RANGE	PACKAGE		
CA3273	-40°C to +85°C	TO-202 Modified SIP		



R.

LOAD

Absolute Maximum Ratings

Thermal Information

Fault Max, Supply Voltage, V _{CC} 40V	
Maximum Operating V _{CC} :	
At $I_0 = 400 \text{mA} (-40^{\circ} \text{C to} +85^{\circ} \text{C Ambient}) \dots 16 \text{V}$	
At $I_0 = 600 \text{ mA} (-40^{\circ} \text{C to } +25^{\circ} \text{C Ambient}) \dots 24 \text{ V}$	
Max. Positive Output Peak Pulse, V _{SW} OpenV _{CC} +12V	
Max. Operating Output Load Current	
Short Circuit Load Current, I _{SC} Internal Limiting	
Reverse Battery13V	

Thermal Resistance θJA Plastic SIP Package +70°C/W Maximum Power Dissipation, PD PD
At +25°C Ambient, T _A (Note 1)1.8W Derate above +25°C (No Heat Sink)14.3mW/°C
Maximum Junction Temperature, T_J (Note 2)
Storage Temperature Range40°C to +150°C Lead Temperature (Soldering 10s max)+265°C

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

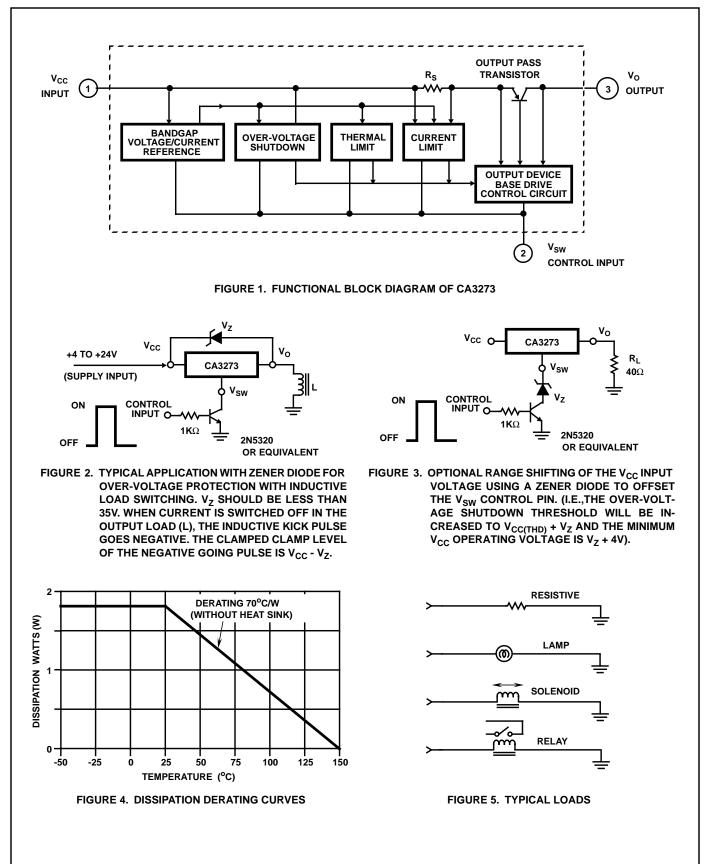
Electrical Specifications T _A = -40°C to +85°C, Unless Otherwise Noted, See Block Diagram for Test Pin Referer

PARAMETERS	SYMBOL	TEST CONDITIONS	MIN	ТҮР	MAX	UNITS
Operating Voltage Range	V _{CC}	$\rm V_{CC}$ Reference to $\rm V_{SW}$	4	-	24	V
Saturation Voltage(V _{CC} - V _O)	V _{SAT}	I_{O} = -400mA, V_{SW} = 0V, V_{CC} = 16V	-	-	0.5	V
Operating Load	RL	V _{SW} = 0V (Switch ON)				
		$T_A = +85^{o}C, V_{CC} = 16V$	40	-	-	Ω
		$T_{A} = +25^{\circ}C, V_{CC} = 24V$	40			Ω
Over-Voltage Shutdown Threshold	V _{CC(THD)}	V_{SW} = 0V, R_L = 1k $\Omega,$ Increase $V_{CC,}$ (V_O goes low)	25	33	40	V
Over-Current Limiting	I _{O(LIM)}	V_{CC} =16V, V_{SW} = 1V (Switch ON)	-	-	1.2	А
Over-Temperature Limiting	T _{LIM}		-	150	-	°C
Control Current, Switch ON	I _{SW}	$V_{CC} = 16V, V_{SW} = 0V$				
		$I_{O} = 0mA$	-	-15	-	mA
		I _O = -400mA	-	-22	-	mA
Control Current, Max. Load, Switch ON		$V_{CC} = 24V, V_{SW} = 0V,$ $I_{O} = -600mA$	-	-33	-	mA
Max. Control Current, High and	I _{SW(MAX)}	$R_L = 40\Omega, V_{SW} = 1V$				
Low V _{CC}		$V_{CC} = 24V$	-50	-	-	mA
		$V_{CC} = 7V$	-50	-	-	mA
Min. Control Current, No Load,	I _{SW(NL)}	V _O = Open, (Switch OFF)				
Switch OFF		$V_{CC} = 24V, V_{SW} = 23V$	-200	-	+50	μΑ
		V _{CC} = 7V, V _{SW} = 6V	-200	-	+50	μΑ
Output Current Leakage	I _{O(LEAK)}	$V_{O} = 0V, V_{CC} = 16V, $ (Switch OFF)				
		V _{SW} =16V	-100	-	+100	μΑ
		V _{SW} =15V	-100	-	+100	μA

NOTES:

1. The calculation for dissipation and junction temperature rise due to dissipation is: $P_D = (V_{CC} - V_O) \times I_O + V_{CC} \times I_{SW}$ and $T_J = T_A + P_D \times \theta_{JA}$ where T_J is device junction temperature, T_A is ambient temperature and θ_{JA} is the junction-to-ambient thermal resistance.

2. Thermal limiting occurs at +150°C on the chip.



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